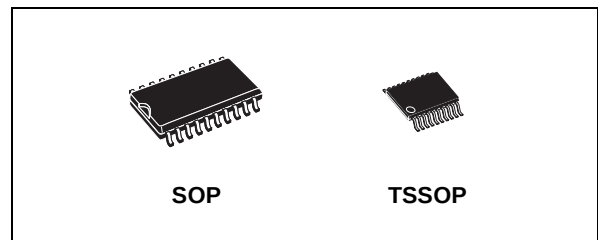




74LVQ573

LOW VOLTAGE CMOS OCTAL D-TYPE LATCH WITH 3 STATE OUTPUTS NON INVERTING

- HIGH SPEED:
 $t_{PD} = 5.8 \text{ ns (TYP.) at } V_{CC} = 3.3 \text{ V}$
- COMPATIBLE WITH TTL OUTPUTS
- LOW POWER DISSIPATION:
 $I_{CC} = 4 \mu\text{A (MAX.) at } T_A = 25^\circ\text{C}$
- LOW NOISE:
 $V_{OLP} = 0.5\text{V (TYP.) at } V_{CC} = 3.3\text{V}$
- 75Ω TRANSMISSION LINE DRIVING CAPABILITY
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 12\text{mA (MIN) at } V_{CC} = 3.0 \text{ V}$
- PCI BUS LEVELS GUARANTEED AT 24 mA
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \approx t_{PHL}$
- OPERATING VOLTAGE RANGE:
 $V_{CC(OPR)} = 2\text{V to } 3.6\text{V (1.2V Data Retention)}$
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 573
- IMPROVED LATCH-UP IMMUNITY



ORDER CODES

PACKAGE	TUBE	T & R
SOP	74LVQ573M	74LVQ573MTR
TSSOP		74LVQ573TTR

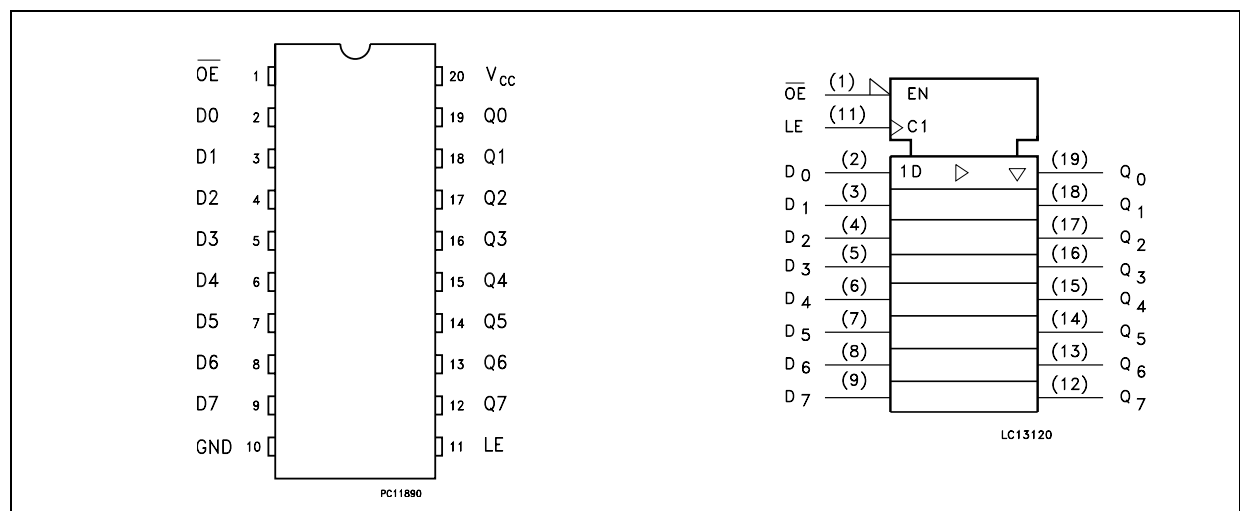
While the LE input is held at a high level, the Q outputs will follow the data input precisely. When the LE is taken low, the Q outputs will be latched precisely at the logic level of D input data. While the ($\overline{OE}$) input is low, the 8 outputs will be in a normal logic state (high or low logic level) and while high level the outputs will be in a high impedance state. In order to enhance PC board layout, the 74LVQ573 offers a pinout having inputs and outputs on opposite side of the package. All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

DESCRIPTION

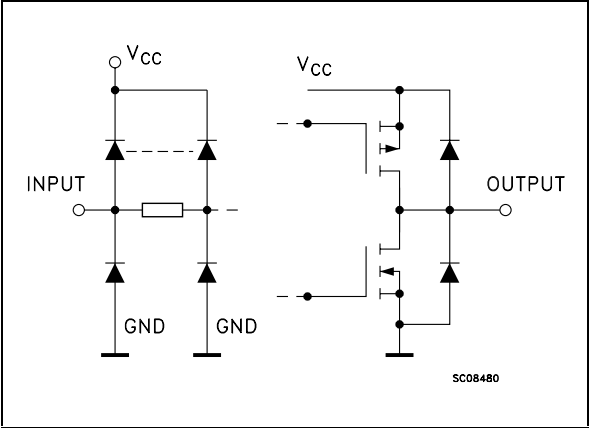
The 74LVQ573 is a low voltage CMOS OCTAL D-TYPE LATCH with 3 STATE OUTPUTS NON INVERTING fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology. It is ideal for low power and low noise 3.3V applications.

These 8 bit D-Type latch are controlled by a latch enable input (LE) and an output enable input ($\overline{OE}$).

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

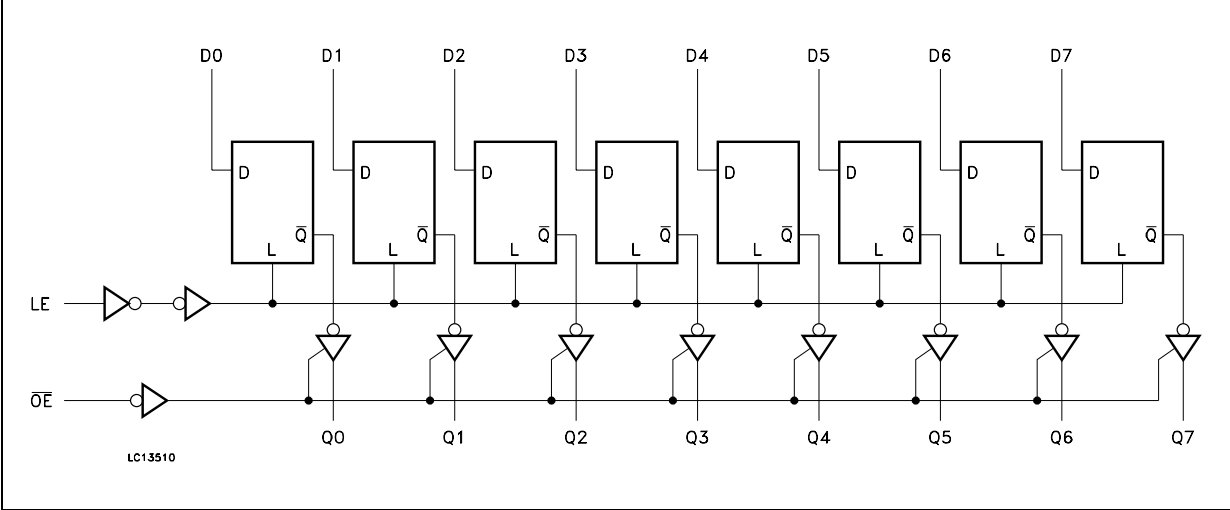
PIN No	SYMBOL	NAME AND FUNCTION
1	$\overline{OE}$	3 State Output Enable Input (Active LOW)
2, 3, 4, 5, 6, 7, 8, 9	D0 to D7	Data Inputs
12, 13, 14, 15, 16, 17, 18, 19	Q0 to Q7	3-State Latch Outputs
11	LE	Latch Enable Input
10	GND	Ground (0V)
20	V _{CC}	Positive Supply Voltage

TRUTH TABLE

INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
H	X	X	Z
L	L	X	NO CHANGE*
L	H	L	L
L	H	H	H

X : Don't Care
Z : High Impedance
* : Q outputs are latched at the time when the LE input is taken low logic level

LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to $V_{CC} + 0.5$	V
V_O	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 50	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 400	mA
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage (note 1)	2 to 3.6	V
V_I	Input Voltage	0 to V_{CC}	V
V_O	Output Voltage	0 to V_{CC}	V
T_{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time $V_{CC} = 3.0V$ (note 2)	0 to 10	ns/V

1) Truth Table guaranteed: 1.2V to 3.6V

2) V_{IN} from 0.8V to 2V

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{IH}	High Level Input Voltage	3.0 to 3.6		2.0			2.0		2.0		V
V _{IL}	Low Level Input Voltage					0.8		0.8		0.8	V
V _{OH}	High Level Output Voltage	3.0	I _O = -50 μA	2.9	2.99		2.9		2.9		V
			I _O = -12 mA	2.58			2.48		2.48		
			I _O = -24 mA				2.2		2.2		
V _{OL}	Low Level Output Voltage	3.0	I _O = 50 μA		0.002	0.1		0.1		0.1	V
			I _O = 12 mA		0	0.36		0.44		0.44	
			I _O = 24 mA					0.55		0.55	
I _I	Input Leakage Current	3.6	V _I = V _{CC} or GND			± 0.1		± 1		± 1	μA
I _{OZ}	High Impedance Output Leakage Current	3.6	V _I = V _{IH} or V _{IL} V _O = V _{CC} or GND			±0.25		± 2.5		± 5.0	μA
I _{CC}	Quiescent Supply Current	3.6	V _I = V _{CC} or GND			4		40		40	μA
I _{OLD}	Dynamic Output Current (note 1, 2)	3.6	V _{OLD} = 0.8 V max				36		25		mA
I _{OHD}			V _{OHD} = 2 V min				-25		-25		mA

1) Maximum test duration 2ms, one output loaded at time

2) Incident wave switching is guaranteed on transmission lines with impedances as low as 75Ω

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{OLP}	Dynamic Low Voltage Quiet Output (note 1, 2)	3.3	C _L = 50 pF		0.5	0.8					V
V _{OLV}				-0.8	-0.6						
V _{IHD}	Dynamic High Voltage Input (note 1, 3)	3.3		2							V
V _{ILD}	Dynamic Low Voltage Input (note 1, 3)	3.3					0.8				

1) Worst case package.

2) Max number of outputs defined as (n). Data inputs are driven 0V to 3.3V, (n-1) outputs switching and one output at GND.

3) Max number of data inputs (n) switching. (n-1) switching 0V to 3.3V. Inputs under test switching: 3.3V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), f=1MHz.

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, R_L = 500 Ω, Input t_r = t_f = 3ns)

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t _{PLH} t _{PHL}	Propagation Delay Time LE to Q	2.7			7.2	11.5		13.5		15.5	ns
		3.3(*)			5.8	9.0		10.5		12.0	
t _{PLH} t _{PHL}	Propagation Delay Time D to Q	2.7			7.2	11.5		13.5		15.5	ns
		3.3(*)			5.8	9.0		10.5		12.0	
t _{PLZ} t _{PHZ}	Output Disable Time	2.7			8.7	14.0		16.0		18.5	ns
		3.3(*)			7.4	11.5		13.5		15.5	
t _{PZL} t _{PZH}	Output Enable Time	2.7			8.5	14.0		16.0		18.5	ns
		3.3(*)			7.5	11.5		13.5		15.5	
t _W	LE Pulse Width HIGH	2.7			2.0	5.0		6.0		6.0	ns
		3.3(*)			1.5	4.0		4.0		4.0	
t _{sL} t _{sH}	Setup Time D to LE HIGH or LOW	2.7			0.0	4.0		4.5		4.5	ns
		3.3(*)			0.0	3.0		3.0		3.0	
t _{hL} t _{hH}	Hold Time D to LE, HIGH or LOW	2.7			0.0	1.5		1.5		1.5	ns
		3.3(*)			0.0	1.5		1.5		1.5	
t _{OSLH} t _{OSHL}	Output To Output Skew Time (note1, 2)	2.7			0.5	1.0		1.0		1.0	ns
		3.3(*)			0.5	1.0		1.0		1.0	

1) Skew is defined as the absolute value of the difference between the actual propagation delay for any two outputs of the same device switching in the same direction, either HIGH or LOW (t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|)

2) Parameter guaranteed by design

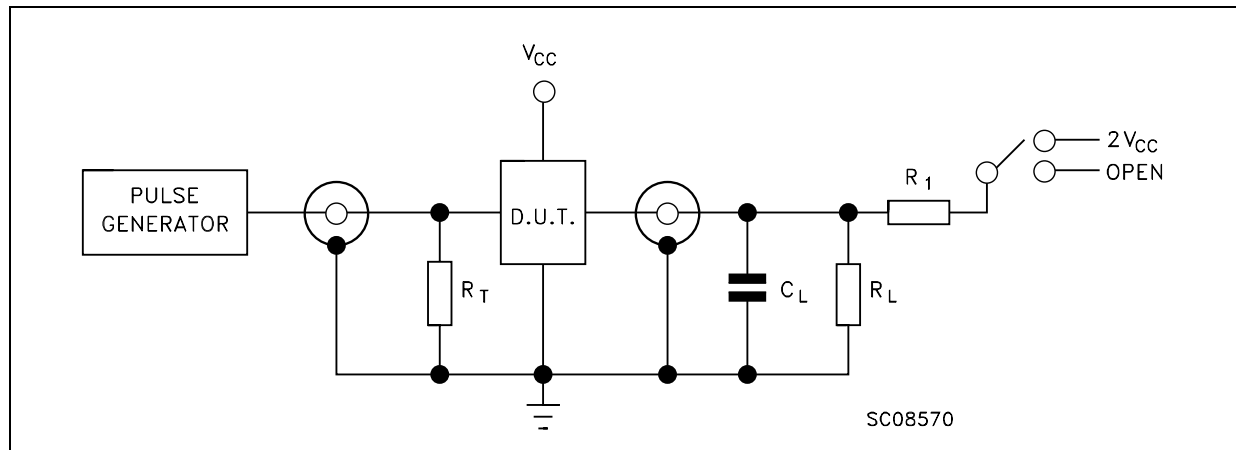
(*) Voltage range is 3.3V ± 0.3V

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C _{IN}	Input Capacitance	3.3			4						pF
C _{OUT}	Output Capacitance	3.3			8						pF
C _{PD}	Power Dissipation Capacitance (note 1)	3.3	f _{IN} = 10MHz		10						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/n$ (per latch)

TEST CIRCUIT



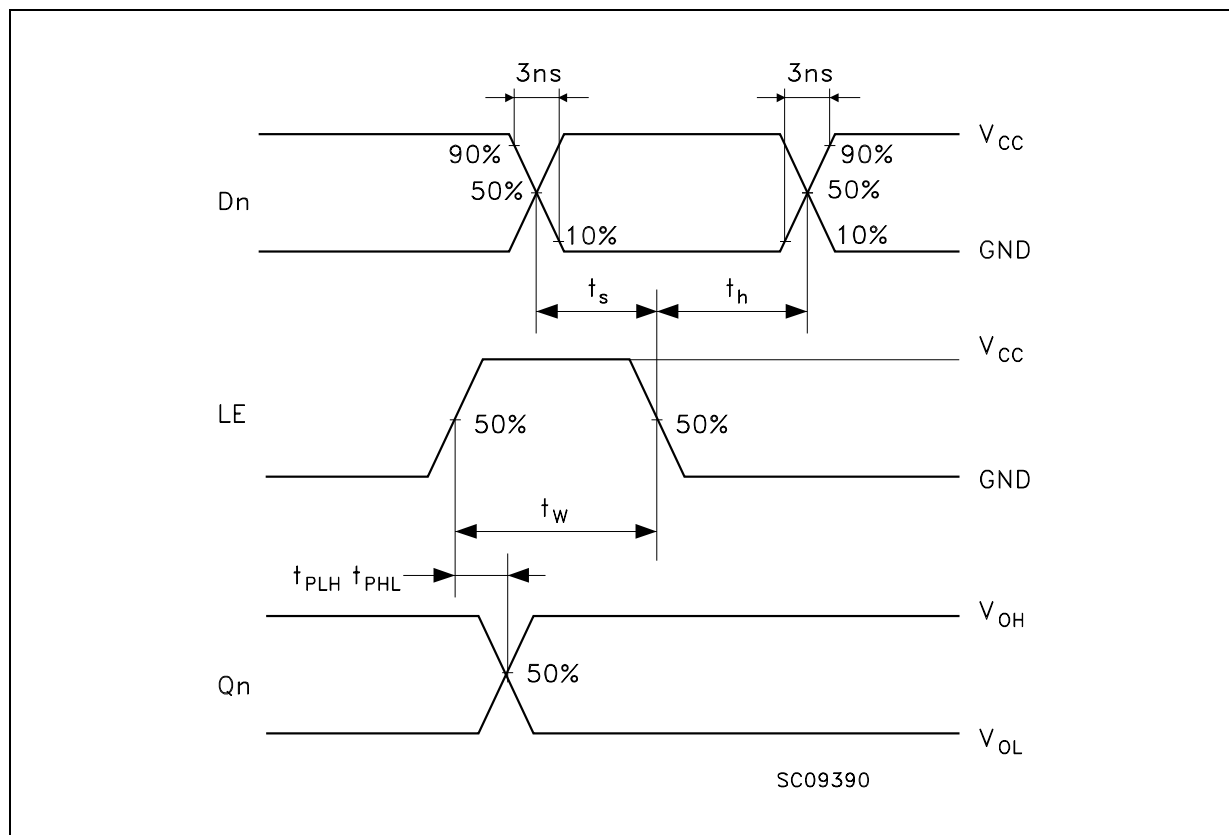
TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	2V _{CC}
t _{PZH} , t _{PHZ}	Open

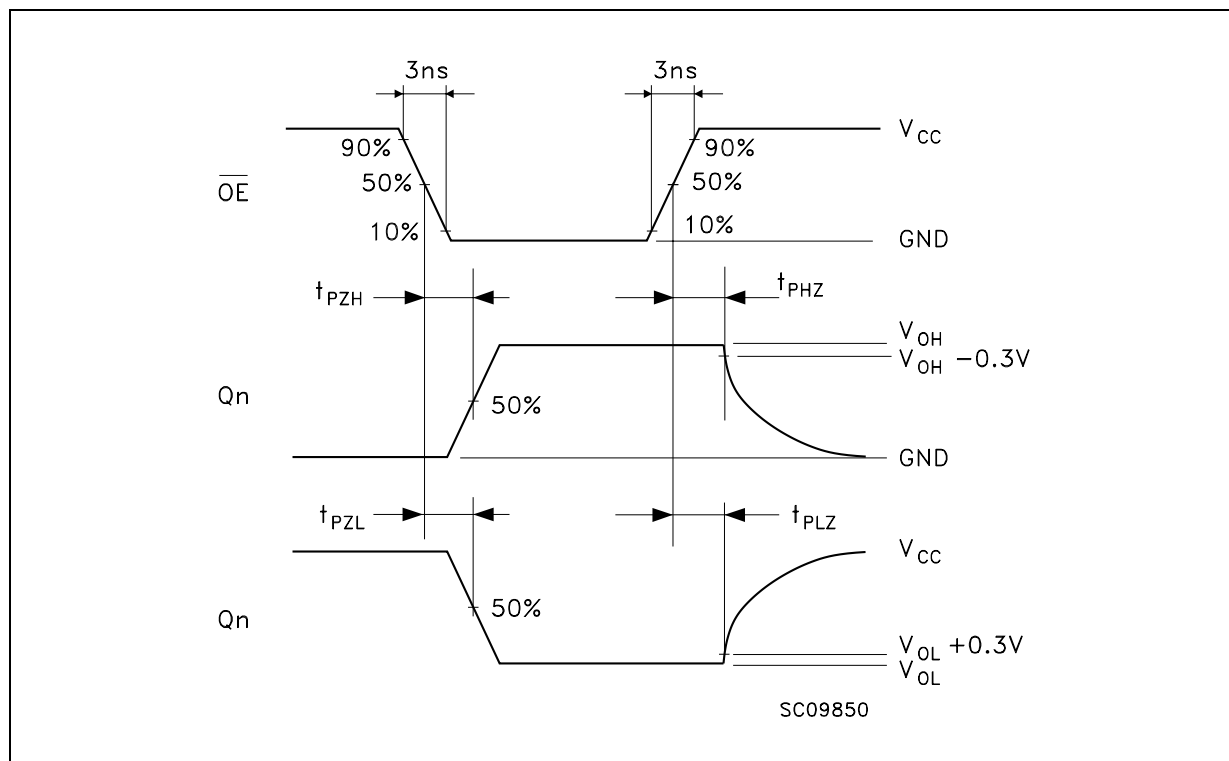
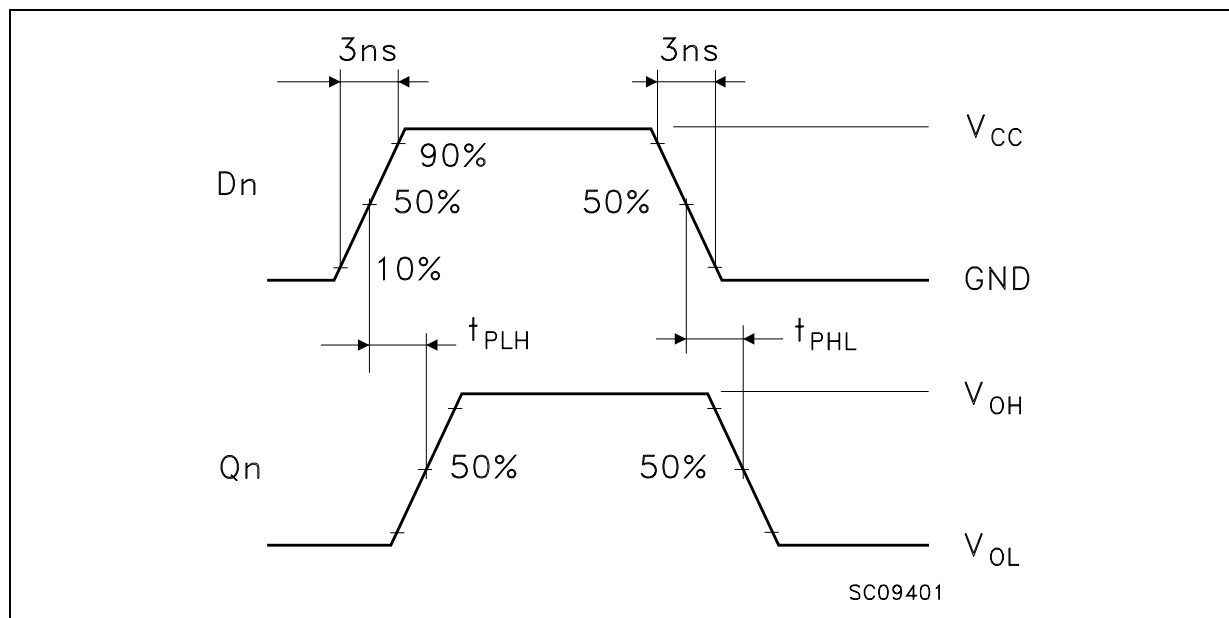
C_L = 50pF or equivalent (includes jig and probe capacitance)

R_L = R₁ = 500Ω or equivalent

R_T = Z_{OUT} of pulse generator (typically 50Ω)

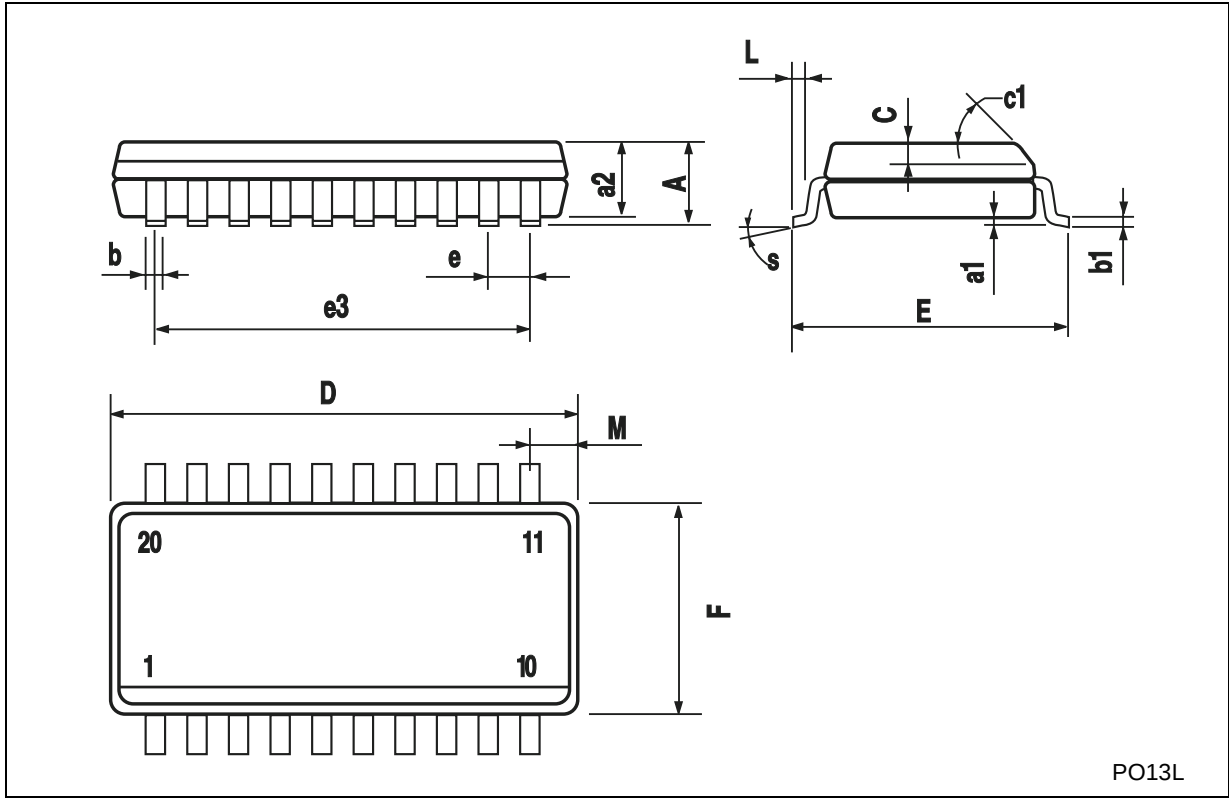
WAVEFORM 1: LE TO Qn PROPAGATION DELAYS, LE MINIMUM PULSE WIDTH, Dn TO LE SETUP AND HOLD TIMES ($f=1\text{MHz}$; 50% duty cycle)



WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIMES ($f=1\text{MHz}$; 50% duty cycle)**WAVEFORM 3: Dn TO Qn PROPAGATION DELAY TIME** ($f=1\text{MHz}$; 50% duty cycle)

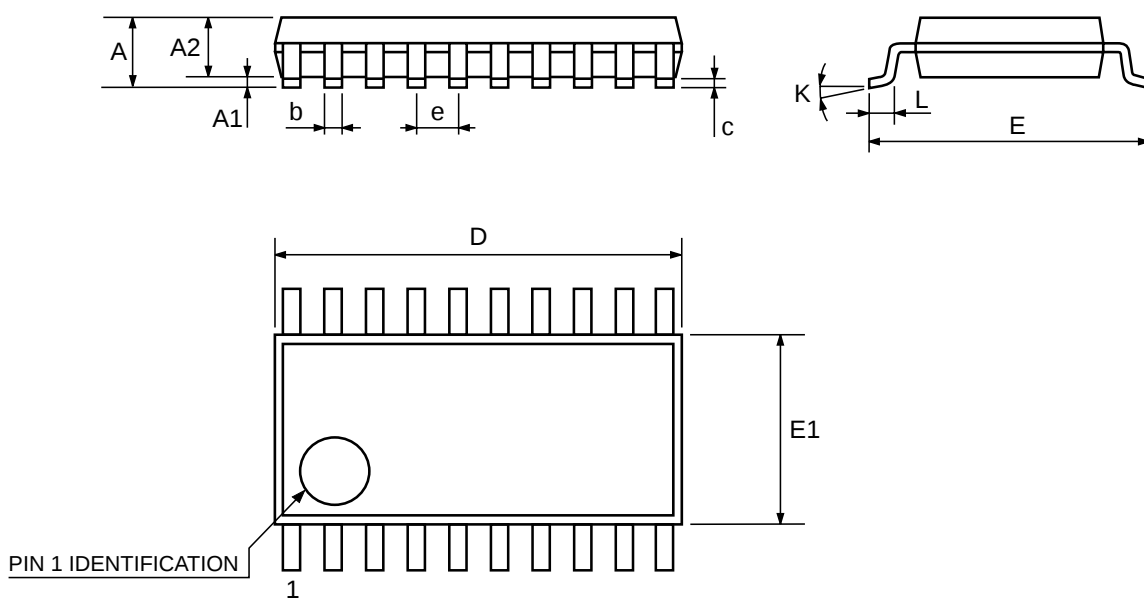
SO-20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.1		0.2	0.004		0.008
a2			2.45			0.096
b	0.35		0.49	0.014		0.019
b1	0.23		0.32	0.009		0.012
C		0.5			0.020	
c1	45° (typ.)					
D	12.60		13.00	0.496		0.512
E	10.00		10.65	0.393		0.419
e		1.27			0.050	
e3		11.43			0.450	
F	7.40		7.60	0.291		0.300
L	0.50		1.27	0.020		0.050
M			0.75			0.029
S	8° (max.)					



TSSOP20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	6.4	6.5	6.6	0.252	0.256	0.260
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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